

In re Appln. of TOTSUKA et al.
Application No. Unassigned

ABSTRACT AMENDMENTS

Replace the Abstract with:

A method of manufacturing a semiconductor device ~~using~~ including a gallium nitride related semiconductor ~~is provided~~. The method include ~~a step of~~ preparing a substrate ~~whose~~ having surface ~~is formed by~~ of a gallium nitride related semiconductor; ~~a nitriding step of~~ contacting the surface with ~~atom-state~~ atomic nitrogen, which is obtained by decomposing a nitrogen-containing gas ~~by means of~~ in a catalytic reaction, to ~~thereby~~ nitride the surface; and ~~an electrode-forming step of~~ forming, on the surface, a gate electrode and source and drain electrodes opposing each other ~~through~~ across the gate electrode.